

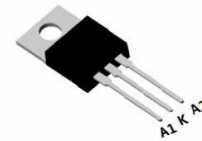
WSB10100T

Power Schottky Barrier Rectifier

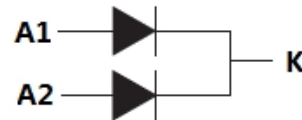
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

Features

- 2x5A average rectified forward current
- Low forward voltage and Low leakage current
- Excellent high junction temperature stability
- High forward surge capability



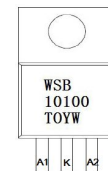
TO-220



Circuit

Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters



TO-220

Marking

Absolute maximum ratings				
Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	100	V
Reverse voltage (DC)		V_R	100	V
Average rectified forward current	Per diode	I_F	5	A
	Per device	I_F	10	A
Peak Forward Surge Current ⁽¹⁾		I_{FSM}	100	A
Junction temperature		T_J	150	°C
Operating temperature		T_{opr}	-55 ~ 150	°C
Storage temperature		T_{stg}	-55 ~ 150	°C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)		$R_{\theta JC}$	2.2	°C/W

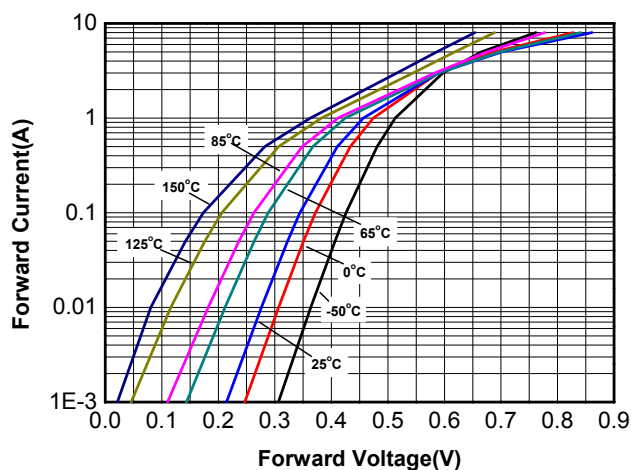
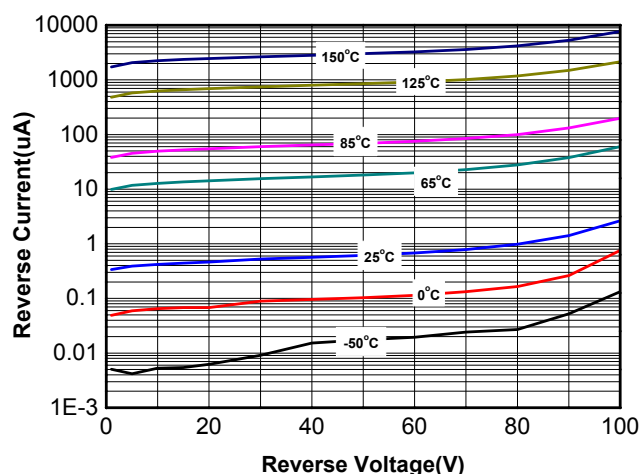
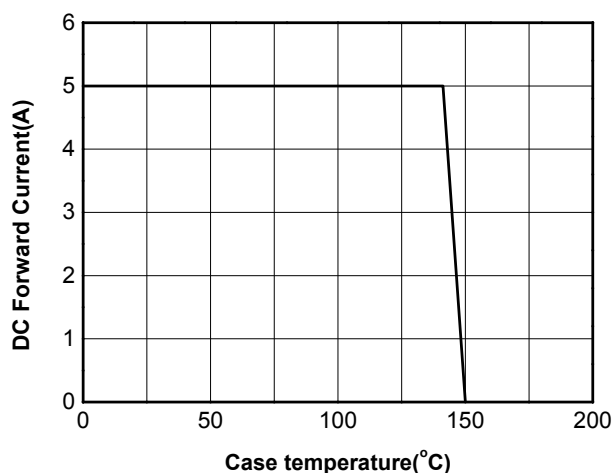
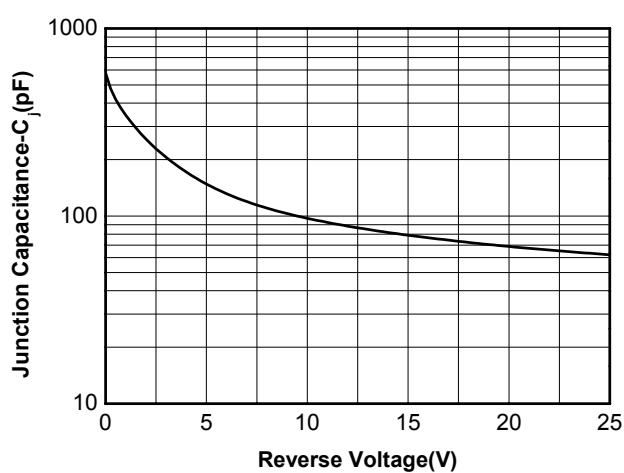
Order information			
Device	Package	Marking	Units/Tube
WSB10100T-3/T	TO-220	WSB10100TOYW ⁽²⁾	50

Note 1: Pulse Width=8.3ms, Single Half Sine Pulse

Note 2: WSB10100= Device code; TO=Special Code; Y=Year; W=Week (A~z)

Electronics characteristics ($T_A=25^\circ\text{C}$, Per diode)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	$I_R=0.5\text{mA}$	100	-	-	V
Forward voltage	V_F	$I_F=5\text{A}$	-	-	0.80	V
Reverse current	I_R	$V_R=100\text{V}$	-	-	0.1	mA
Junction capacitance	C_J	$V_R=25\text{V}$, $F=1\text{MHz}$	-	62	-	pF

Typical characteristics ($T_A=25^\circ\text{C}$, Per diode)

Forward voltage vs. Forward current

Reverse current vs. Reverse voltage

Forward Current Derating Curve

Junction capacitance vs. Reverse voltage

Package outline dimensions
TO-220
